FLL810IQ-4C

L-Band High Power GaAs FET

FEATURES

- Push-Pull Configuration
- High Power Output: 80W
- High PAE: 45%.
- Excellent Linearity
- Suitable for class AB operation.
- Hermetically Sealed Package

DESCRIPTION

The FLL810IQ-4C is an 80 Watt GaAs FET that employs a push-pull design which offers excellent linearity, ease of matching, and greater consistency in covering the frequency band of 3.5 to 3.7 GHz. This new product is uniquely suited for use in WLL applications as it offers high gain, long term reliability and ease of use.



ABSOLUTE MAXIMUM RATINGS (Ambient Temperature Ta=25°C)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V _{DS}		15	V
Gate-Source Voltage	V _{GS}		-5	V
Total Power Dissipation	PT	Tc = 25°C	136	W
Storage Temperature	T _{stg}		-65 to +175	°C
Channel Temperature	T _{ch}		+175	°C

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 12 volts.

2. The forward and reverse gate currents should not exceed 176 and -51.8 mA respectively with

gate resistance of 5Ω .

3. The operating channel temperature (T_{ch}) should not exceed 145°C.

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25°C)

Itom	Symbol	Conditiona	Limits				
liem	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain Current	I _{DSS}	$V_{DS} = 5V, V_{GS} = 0V$	-	8	-	А	
Pinch-Off Voltage	Vp	$V_{DS} = 5V, I_{DS} = 220mA$	-0.1	-0.3	-0.5	V	
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} = -2.2mA	-5	-	-	V	
Output Power	P _{out}		48.0	49.0	-	dBm	
Linear Gain (Note 1)	GL	V _{DS} = 12V f = 3.6 GHz	8.5	9.5	-	dB	
Power-Added Efficiency	η_{add}	I _{DS} = 5.0A Pin = 43.0dBm	-	45	-	%	
Drain Current	I _{DSR}		-	11.5	15.0	A	
Thermal Resistance	R _{th}	Channel to Case	-	0.8	1.1	°C/W	

CASE STYLE: IQ

Note 1: The condition for GL is the same as Pout except Pin = 28.0dBm.







OUTPUT POWER & $\eta_{\mbox{add}}$ vs. INPUT POWER



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			V _{DS} =	= 12V, I _{DS}	= 2500mA				
FREQUENCY	S11		S	S21		S12		S22	
(MHZ)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
2500	.499	-103.9	1.973	-113.4	.017	-111.7	.796	152.9	
2600	.617	-120.1	1.880	-125.9	.017	-134.2	.773	151.8	
2700	.703	-131.7	1.735	-142.2	.016	-149.9	.752	150.1	
2800	.761	-141.4	1.784	-153.8	.016	-167.5	.729	149.5	
2900	.793	-148.6	1.689	-163.9	.017	-176.4	.714	148.0	
3000	.801	-155.5	1.803	-178.8	.017	161.0	.678	146.2	
3100	.783	-162.8	1.949	171.0	.019	136.6	.656	143.9	
3200	.747	-169.1	2.087	154.5	.021	119.4	.604	140.8	
3300	.644	-176.8	2.398	136.9	.024	94.7	.566	138.8	
3400	.492	178.6	2.627	116.1	.031	80.3	.506	137.6	
3500	.315	-166.2	2.798	88.0	.036	48.3	.468	143.3	
3600	.397	-130.1	2.612	59.6	.034	15.7	.504	148.1	
3700	.603	-128.8	2.173	33.1	.031	-8.8	.558	145.3	
3800	.743	-135.6	1.814	13.3	.024	-33.0	.580	136.4	
3900	.825	-143.0	1.493	-5.2	.022	-47.8	.559	125.9	
4000	.878	-148.0	1.222	-20.4	.019	-59.2	.535	113.4	
4100	.910	-152.6	.999	-34.6	.019	-67.0	.483	97.7	
4200	.937	-156.1	.849	-46.9	.017	-76.4	.418	78.8	
4300	.949	-159.8	.735	-55.8	.018	-86.6	.376	53.9	
4400	.953	-162.7	.681	-67.5	.018	-96.7	.343	18.9	
4500	.956	-165.1	.666	-82.1	.020	-107.9	.386	-17.4	

S-PARAMETERS

Note: This S-Parameter data shows measurements performed on a single-ended push-pull FET. These parameters should be used to determine the calculated Push-Pull S-Parameter amplifier designs.



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